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Inventor: E. Morita) Examiner: M. Anderson
Serial No.: 09/726,860)
Title: Method of Manufacturing Crystal of III-V...)
Atty. Docket No. 9792909-4715)
Group Unit: 1765

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Response C to First Non Final Office Action dated 23 July 2002

In response to the Non Final Office Action dated 23 July 2002, the applicant responds as follows.

A. In the Claims

1. (amended) A method of manufacturing a crystal of a III-V compound of the nitride system, the method including:

a first growth step to form a first crystal layer, the first crystal layer further having a surface, by growing a crystal of a III-V compound of the nitride system on a surface of a basal body;

a first mask forming step to form a first mask pattern on the surface of the first crystal layer;

a first etching step to etch the first crystal layer through the first mask pattern;

a second growth step to form a second crystal layer, the second crystal layer further having a surface, by growing a crystal of a III-V compound of the nitride system from the first crystal layer;

a second mask forming step to form a second mask pattern on the surface of the second crystal layer and ensuring that the second mask overlies a window in the first mask;